

2SK2393

Silicon N Channel MOS FET

REJ03G1010-0300 Rev.3.00 Apr 28, 2009

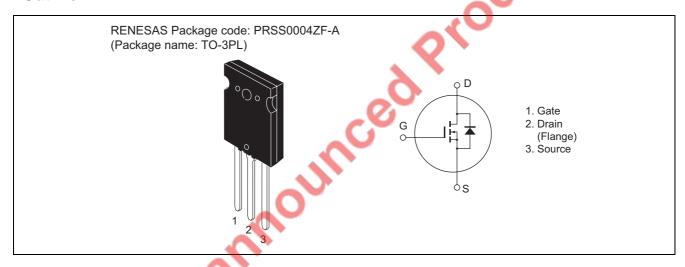
Application

High voltage / High speed power switching

Features

- Low on-resistance, High breakdown voltage
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator, motor control

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

ltem	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	1500	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	8	A
Drain peak current	I _{D(pulse)} *1	20	A
Body to drain diode reverse drain current	I _{DR}	8	A
Channel dissipation	Pch*2	200	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1 %

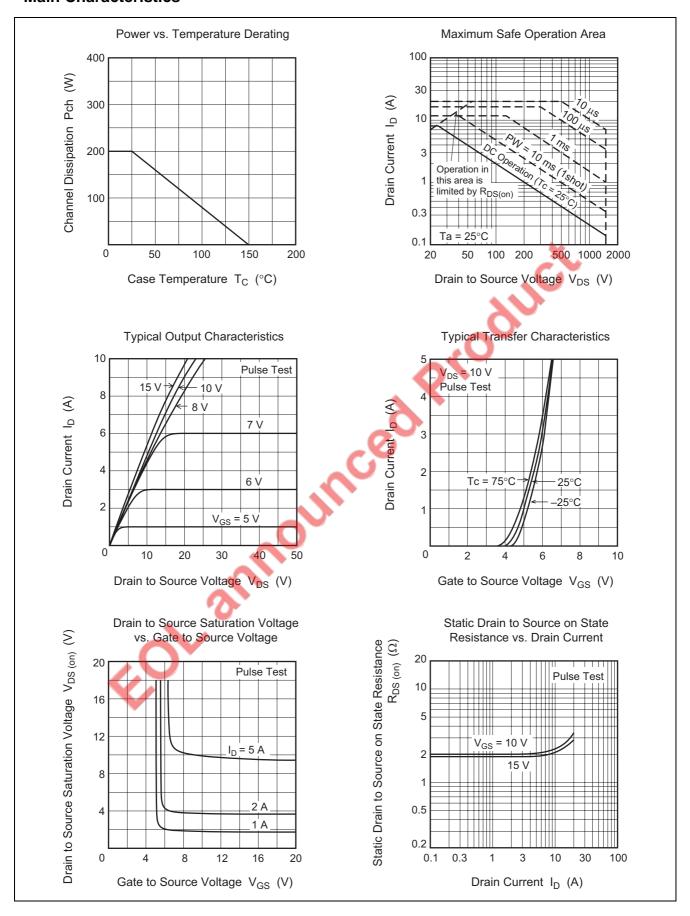
2. Value at Tc = 25°C

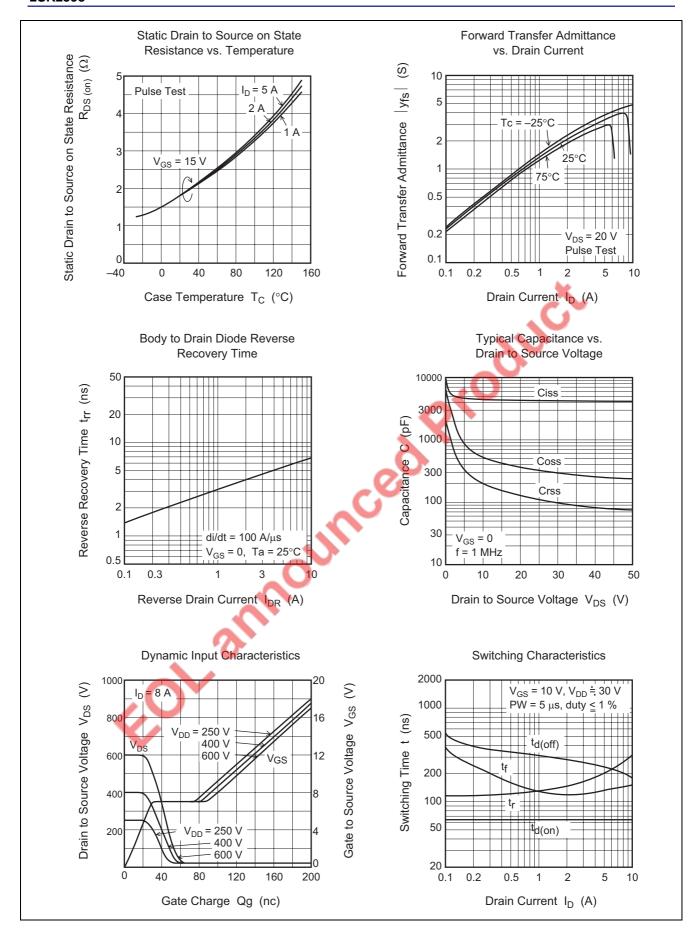
Electrical Characteristics

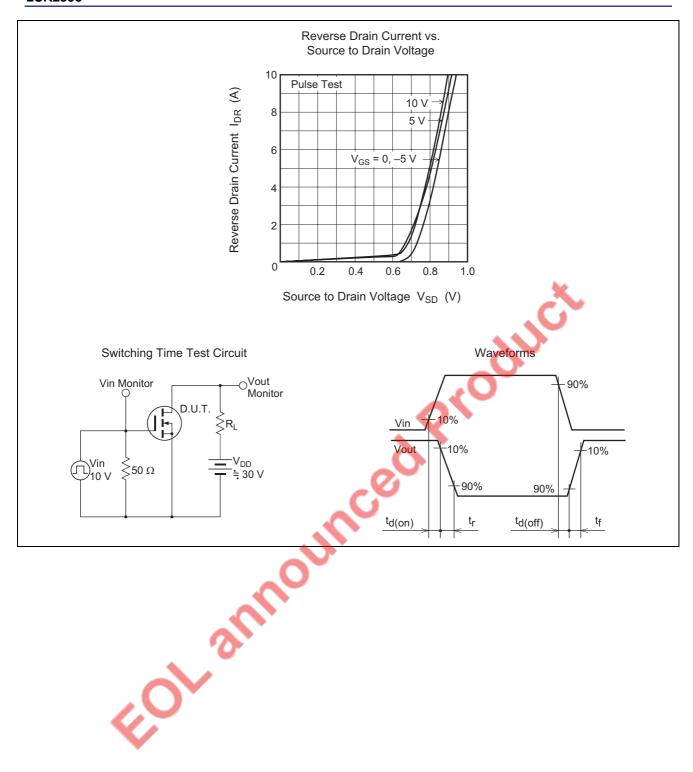
 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	1500	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0^{*1}$
Gate to source leak current	I _{GSS}	_	_	±1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	500	μA	V _{DS} = 1200 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS(off)}	2.0	_	4.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state	R _{DS(on)}	_	1.9	2.8	Ω	$I_D = 4 \text{ A}, V_{GS} = 15 \text{ V}^{*3}$
resistance	, ,					
Forward transfer admittance	y _{fs}	1.8	3.0	_	S	$I_D = 4 A, V_{DS} = 20 V^{*3}$
Input capacitance	Ciss	_	4370	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	560	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	200	_	pF]
Turn-on delay time	t _{d(on)}	_	75	_	ns	$I_D = 4 A, V_{GS} = 10 V,$
Rise time	t _r	_	180	_	ns	$R_L = 7.5 \Omega$
Turn-off delay time	t _{d(off)}	_	260	_	ns	
Fall time	t _f	_	125	_	ns	
Body to drain diode forward voltage	V _{DF}	_	0.9	_	V 🦠	$I_F = 8 A, V_{GS} = 0$
Body to drain diode reverse	t _{rr}	_	6.5	_	μs	$I_F = 8 \text{ A}, V_{GS} = 0,$
recovery time						di _F / dt = 100 A / μs
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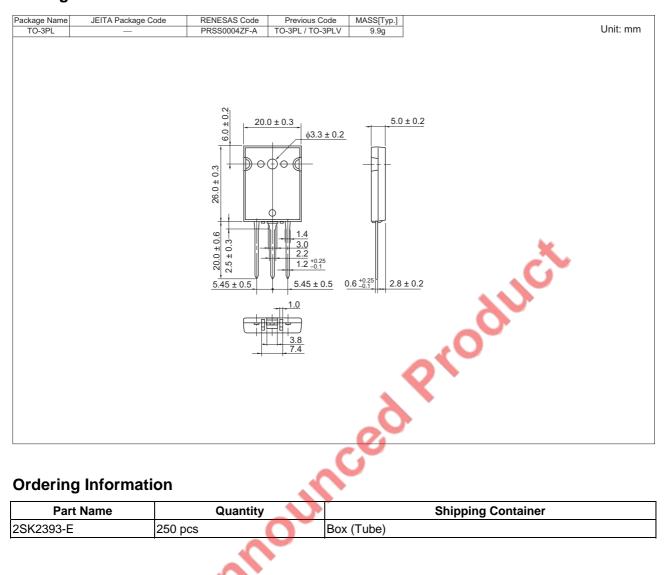
Main Characteristics







Package Dimensions



Ordering Information

Part Name	Quantity	N.	Shipping Container						
2SK2393-E	250 pcs		Box (Tube)						
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